



#### **General Description**

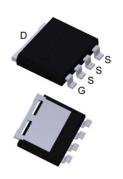
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

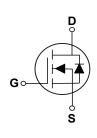
BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	Ι <sub>D</sub>
40 V	0.7 mΩ	455 A

#### **Features**

- $R_{DS(ON)} \leq 0.7 m\Omega@V_{GS} = 10V$
- · Improved dv/dt Capability
- · Fast Switching
- · Green Device Available

#### LFPAK8080 Pin Configuration





#### **Applications**

- · DC-DC Converters
- · Body Control Electronics
- · LED Lighting

Ordering Information					
Part No. Remark Package					
LFMND0P7	Halogen Free	LFPAK8080			
LFMND0P7-A	AEC-Q101 qualified (NOTE 1)	LFF AROUGU			

Absolute Maximu	Absolute Maximum Ratings T <sub>c</sub> =25°C unless otherwise noted						
Symbol	Parameter	Rating	Units				
$V_{DS}$	Drain-Source Voltage	40	V				
$V_{GS}$	Gate-Source Voltage	±20	V				
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> =25°C)	455	Α				
I <sub>DM</sub>	Drain Current - Pulsed (NOTE 2)	1835	Α				
E <sub>AS</sub>	Single Pulse Avalanche Energy (L=0.1mH)	500	mJ				
I <sub>AS</sub>	Single Pulse Avalanche Current (L=0.1mH)	100	Α				
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> =25°C)	417	W				
$T_J$	Operating Junction Temperature Range	-55 to 175	°C				
T <sub>STG</sub>	Storage Temperature Range	-55 to 175	°C				
Marking Code		ND0P7					

Thermal Characteristics						
Symbol	Parameter	Rating	Unit			
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	28	°C/W			
$R_{ heta JC}$	Thermal Resistance Junction to Case	0.36	°C/W			





### Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)

#### **Off Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS}$ =0V , $I_D$ =1mA	40			V
I <sub>DSS</sub>	Drain-Source Leakage Current	$V_{DS}$ =32V , $V_{GS}$ =0V			1	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}$ =±20V , $V_{DS}$ =0V			±100	nA

#### On Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V , I <sub>D</sub> =25A		0.54	0.7	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=250uA$	2.0		4.0	V

#### **Dynamic and switching Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
$Q_g$	Total Gate Charge			116		
$Q_{gs}$	Gate-Source Charge	$V_{DD}$ =20V , $V_{GS}$ =10V , $I_{D}$ =25A		36.5		nC
$Q_{gd}$	Gate-Drain Charge			10		
$T_{d(on)}$	Turn-On Delay Time			28.6		
T <sub>r</sub>	Rise Time	$V_{DD}$ =20V , $V_{GS}$ =10V , $R_{G}$ =5 $\Omega$ ,		39.1		nS
$T_{d(off)}$	Turn-Off Delay Time	I <sub>D</sub> =25A		98.2		113
T <sub>f</sub>	Fall Time			48		
C <sub>iss</sub>	Input Capacitance			9985		
$C_{oss}$	Output Capacitance	$V_{DS}$ =20V , $V_{GS}$ =0V , f=1MHz		5746		pF
$C_{rss}$	Reverse Transfer Capacitance			109		
$R_g$	Gate Resistance	$V_{GS}$ =0V , $V_{DS}$ =0V , f=1MHz		1.9		Ω

### **Drain-Source Diode Characteristics and Ratings**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
$V_{SD}$	Diode Forward Voltage	V <sub>GS</sub> =0V , I <sub>S</sub> =20A			1.2	V
$T_{rr}$	Body Diode Reverse Recovery Time	I₅=25A . di/dt=100A/us		116		nS
$Q_{rr}$	Body Diode Reverse Recovery Charge	11;-23A , di/dt-100A/d5		338.1		nC

#### NOTES:

- 1. Qualified to AEC-Q101 standards for high reliability, but do not have all the necessary attributes of automotive grade products.
- 2. Repetitive Rating: Pulsed width limited by maximum junction temperature.
- 3. The data tested by pulsed , pulse width  $\leq$  300us , duty cycle  $\leq$  2%.
- 4. Essentially independent of operating temperature.





#### **Characteristics Curves**

FIG. 1-Continuous Drain Current vs. T<sub>C</sub>

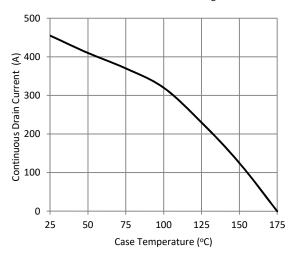


FIG. 2-Normalized  $R_{DS(ON)}$  vs.  $T_J$ 

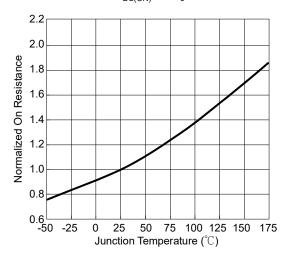


FIG. 3- $V_{th}$  vs.  $T_J$ 

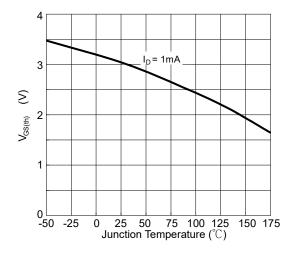


FIG. 4-Gate Charge Characteristics

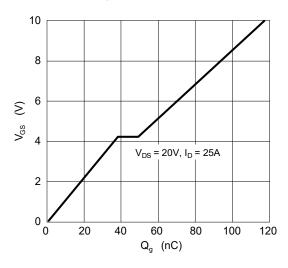


FIG. 5-Transient Thermal Resistance

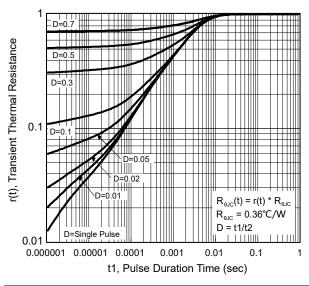
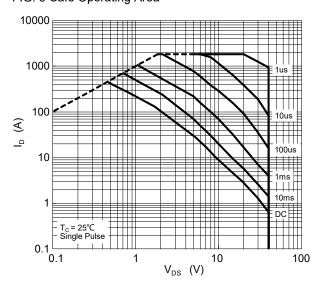


FIG. 6-Safe Operating Area

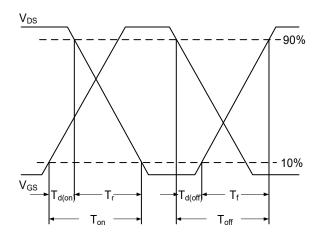




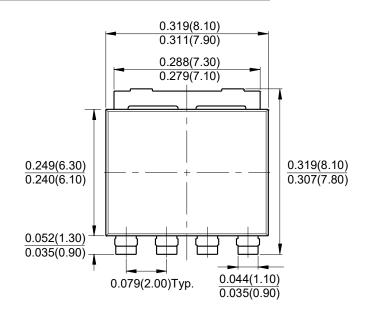


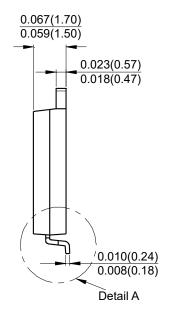
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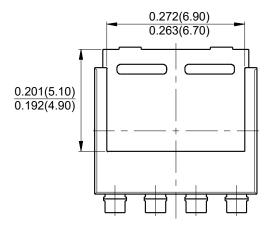
#### FIG. 7-Switching Time Waveform

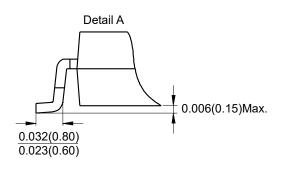


#### **Package Outline Dimensions**









#### LFPAK8080

Dimensions in inches and (millimeters)





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